

MA2C859

Silicon epitaxial planar type

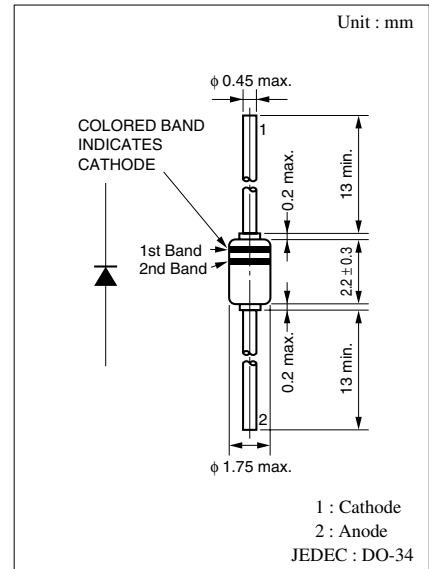
For band switching

■ Features

- Extra-small DHD envelope, allowing to insert into a 5 mm pitch hole
- Less voltage dependence of the terminal capacitance C_t
- Low forward dynamic resistance r_f
- Optimum for a band switching of a tuner

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	35	V
Forward current (DC)	I_F	100	mA
Operating ambient temperature	T_{opr}	-25 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +100	$^\circ\text{C}$



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC) ^{*1}	I_R	$V_R = 33$ V			100	nA
Forward voltage (DC)	V_F	$I_F = 100$ mA			1.0	V
Terminal capacitance	C_t	$V_R = 6$ V, $f = 1$ MHz		0.8	1.2	pF
Forward dynamic resistance	r_f^{*2}	$I_F = 2$ mA, $f = 100$ MHz		0.5	0.65	Ω
	r_f^{*3}			0.77	0.98	Ω

Note) 1. Rated input/output frequency: 100 MHz

2. *1 : Measurement in light shielded condition

*2 : r_f measuring instrument: Nihon Koshuha MODEL TDC-121A Lead length 5mm

*3 : r_f measuring instrument: YHP 4191A Lead length 5mm

■ Cathode Indication

Type No.	MA2C859	
Color	1st Band	Black
	2nd Band	Blue

